

Oxygen diffusion in amorphous and partially crystalline gallium oxide

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Electronic Supplementary Information:

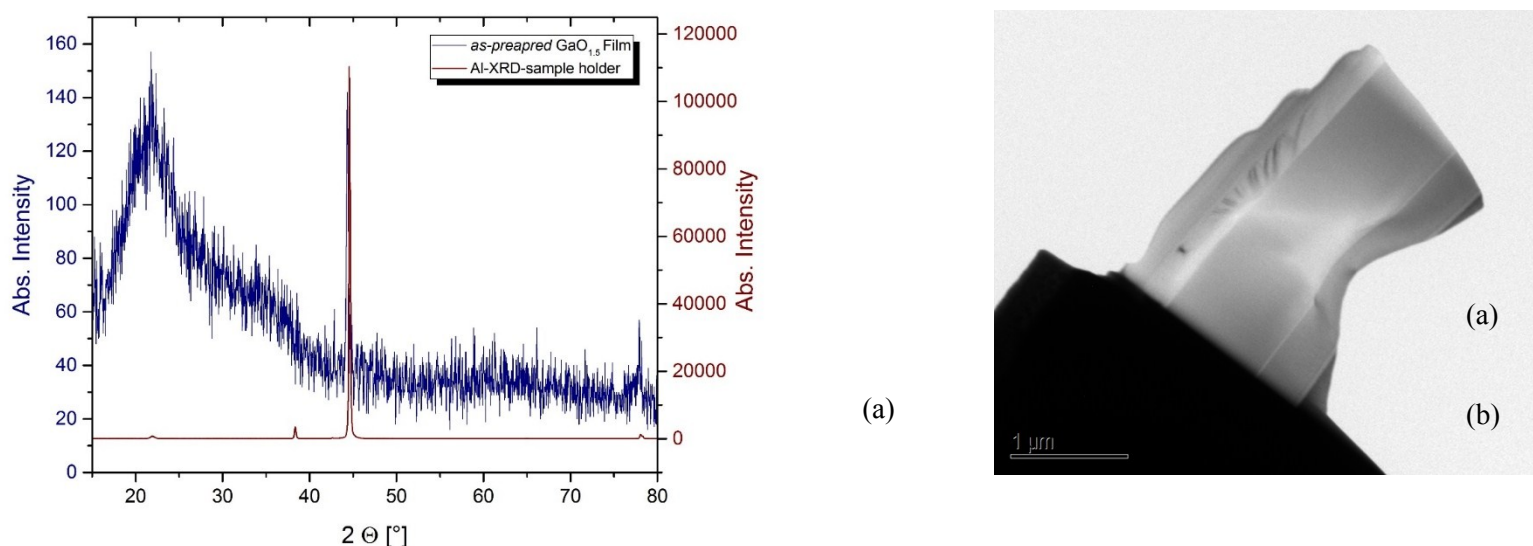


Figure 1 (a) Diffractogram of an amorphous, stoichiometric gallium oxide (a-GaO_{1.5}) thin films (blue) as well as the XRD sample holder made of aluminium (red). (b) Overview of a TEM image of a FIB-lamella of an as-prepared a-GaO_{1.5} thin film.

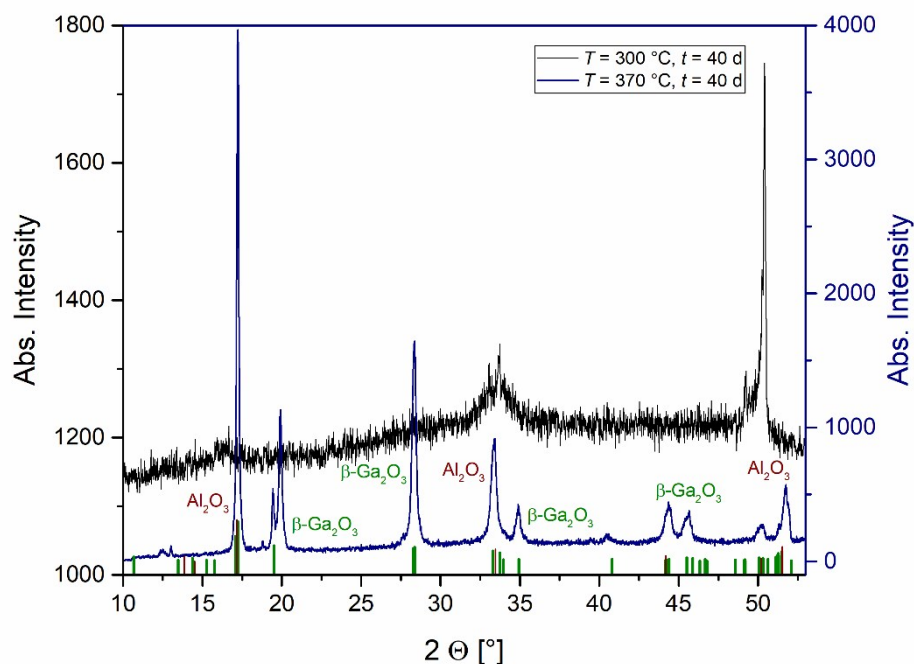


Figure 2 Comparison of diffractograms of a-GaO_{1.5} thin films after annealing at $T = 300$ °C and $T = 370$ °C for $t = 40$ d. The red symbols represent the aluminium substrate and the green symbols represent β-Ga₂O₃.²³